Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS IV)

# **TPC8113**

Lithium Ion Battery Applications
Notebook PC Applications
Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance:  $RDS(ON) = 8 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance:  $|Y_{fs}| = 23 \text{ S (typ.)}$
- Low leakage current:  $IDSS = -10 \mu A (max) (VDS = -30 V)$
- Enhancement-mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V } (V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA})$

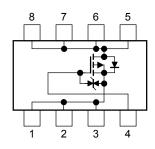
# 0.595TYP 1.27 1, 2, 3 SOURCE 4 GATE 5, 6, 7, 8 DRAIN JEDEC — JEITA — TOSHIBA 2-6J1B

Weight: 0.080 g (typ.)

# Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-30	1
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		VDGR	-30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain ourrant	DC (Note 1)	\$	-11	A
Drain current	Pulse (Note 1)	I <sub>DP</sub>	-44	A
Drain power dissipation (t = 10 s) (Note-2a)		R <sub>D</sub>	1,9	W
Drain power dissipation (t = 10 s) (Note 2b)		PD	1.0	W
Single pulse avalanche energy (Note 3)		EAS	31.5	mJ
Avalanche current		<b>TAR</b>	) –11	Α
Repetitive avalanche energy (Note 2a) (Note 4)		EAR	0.19	mJ
Channel temperature		) T <sub>ch</sub>	150	°C
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C
/ /	/ / /			

### **Circuit Configuration**



Note: (Note 1), (Note 2), (Note 3) and (Note 4): See the next page.

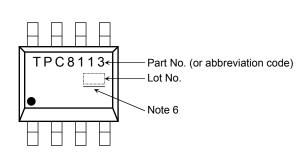
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

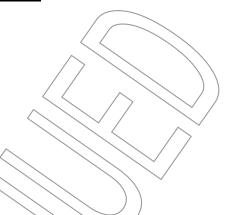
This transistor is an electrostatic-sensitive device. Please handle with caution.

### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W	

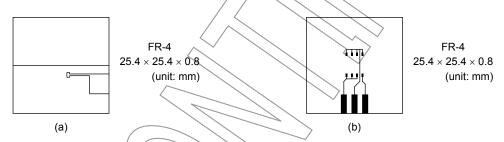






Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)



Note 3:  $V_{DD} = -24 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 0.2 mH,  $R_{G} = 25 \Omega$ ,  $I_{AR} = -11 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

\* Weekly code: (Three digits)

Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

Year of manufacture
(The last digit of the calendar year)

Note 6: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

2 2009-09-29

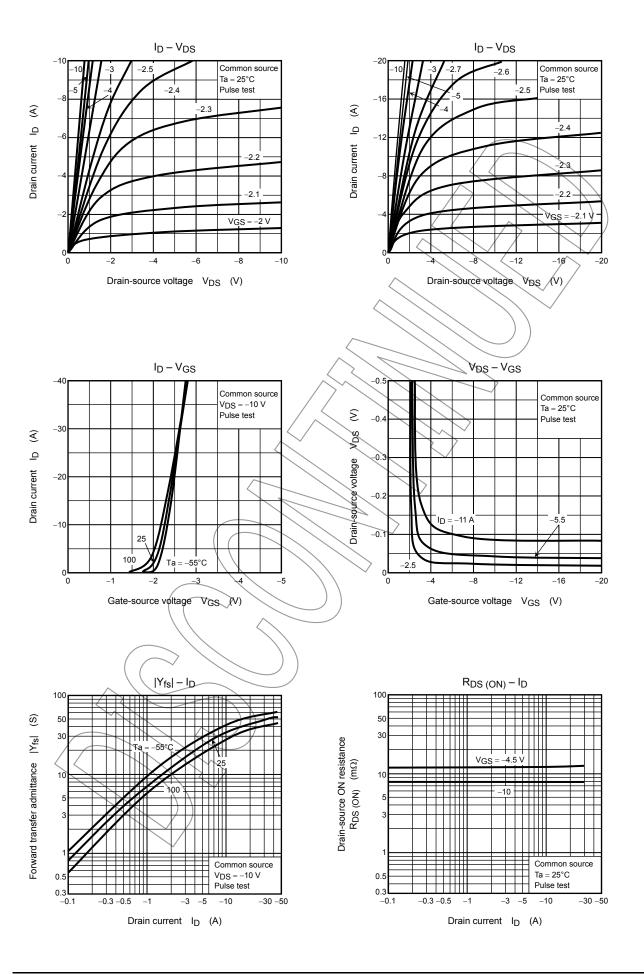
## **Electrical Characteristics (Ta = 25°C)**

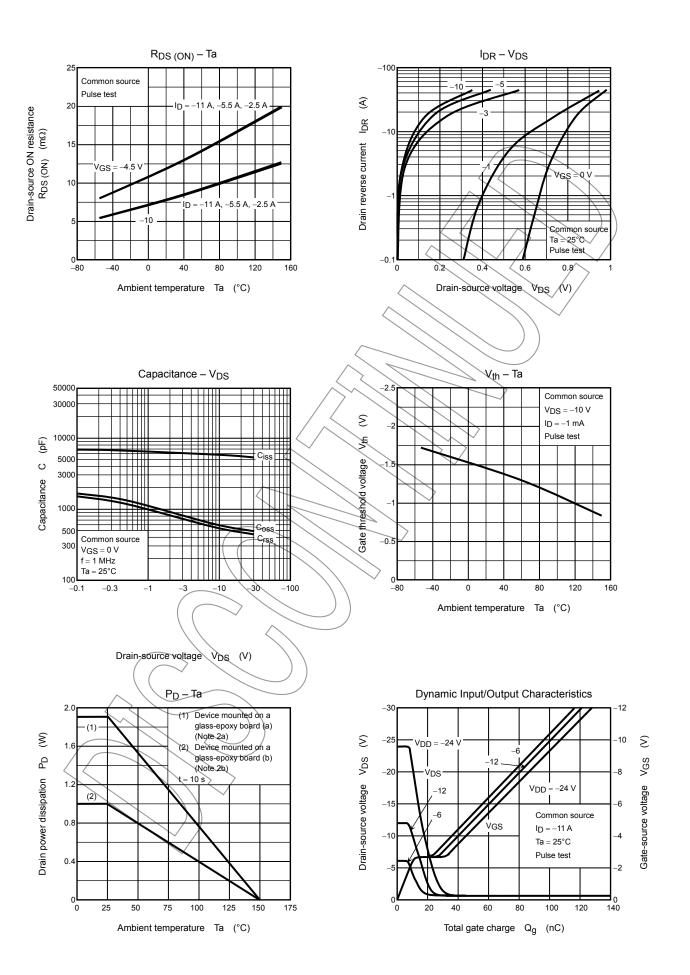
Charact	eristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-OFF current	t	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10$ mA, $V_{GS} = 0$ V	-30	_	_	V
		V <sub>(BR) DSX</sub>	$I_D = -10$ mA, $V_{GS} = 20$ V	-15			v
Gate threshold voltage	е	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	0.8	/	-2.0	V
Drain-source ON resistance		D== (=)	$V_{GS} = -4 \text{ V}, I_D = -5.5 \text{ A}$	y	12	18	mΩ
		R <sub>DS</sub> (ON)	$V_{GS} = -10 \text{ V}, I_D = -5.5 \text{ A}$	1	8	10	
Forward transfer adm	ittance	Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -5.5 \text{ A}$	17	23	(+)	S
Input capacitance		C <sub>iss</sub>		/	4500	\ \ \	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	¥	540/	> _	pF
Output capacitance		Coss			650	_	
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> 0 V 7 I <sub>D</sub> = 5.5 A	+	6	_	
	Turn-ON time	t <sub>on</sub>	-10 V L C C C C C C C C C C C C C C C C C C		13		ns
	Fall time	t <sub>f</sub>	R 0 M 47	$\stackrel{ }{>}$	120		115
	Turn-OFF time	t <sub>off</sub>	$V_{DD} \simeq -15 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10 \text{ µs}$		340		
Total gate charge (gate-source plus gate	e-drain)	Qg	$V_{DD} \simeq -24 \text{ V}, V_{GS} = -10 \text{ V},$	_	107	_	
Gate-source charge 1		Q <sub>gs1</sub>	$N_{D} = -11 \text{ A}$	_	12	_	nC
Gate-drain ("miller") charge		Qgd		_	20	_	

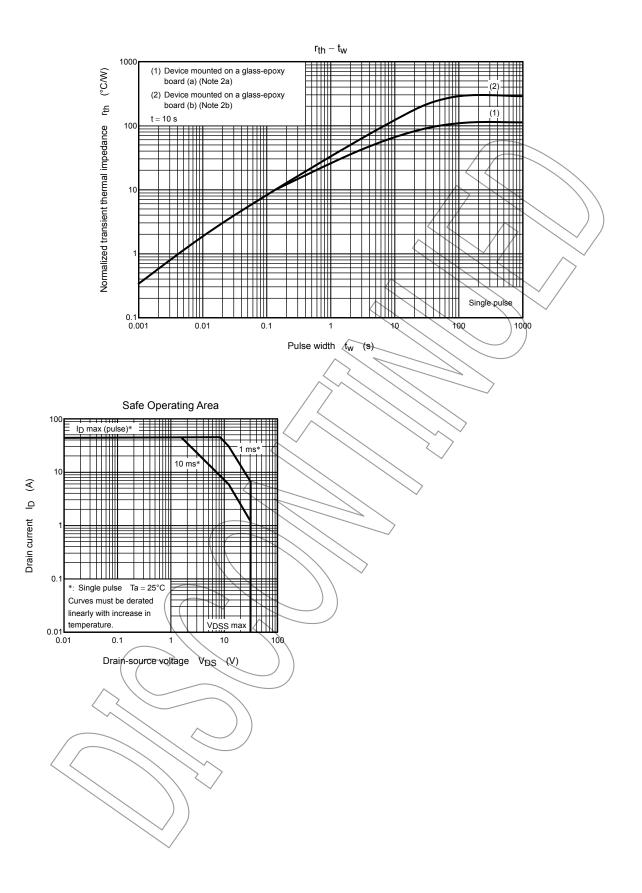
# Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note-1)	1 <sub>DRP</sub>	) —	_	_	-44	Α
Forward voltage (diode)	VDSF TDR	= -11 A, V <sub>GS</sub> = 0 V	_	_	1.2	V

3 2009-09-29







6 2009-09-29

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